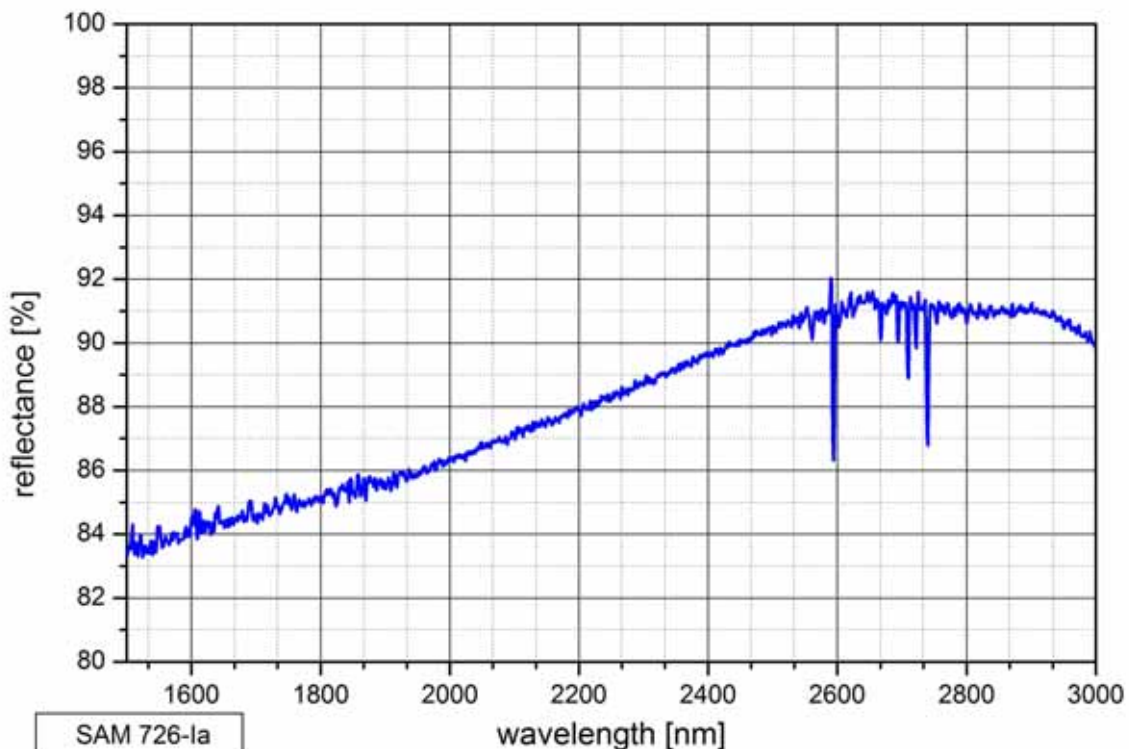


SAM™ Data Sheet SAM-2900-9-10ps-x, $\lambda = 2900 \text{ nm}$

Laser wavelength	$\lambda = 2900 \text{ nm}$
High reflection band (R > 90%)	$\lambda = 2400 \dots 3000 \text{ nm}$
Absorbance	$A_0 = 9 \%$
Modulation depth	$\Delta R = 4 \%$
Non-saturable loss	$A_{ns} = 5 \%$
Saturation fluence	$\Phi_{sat} = 150 \mu\text{J}/\text{cm}^2$
Relaxation time constant	$\tau \sim 10 \text{ ps}$
Damage threshold	$\Phi_{sat} = 2 \text{ mJ}/\text{cm}^2$
Chip area	4 mm x 4 mm; other dimensions on request
Chip thickness	620 μm
Reverse design	the absorber layer is illuminated through the 620 μm thick GaAs wafer
Mounting option x denotes the type of mounting as follows:	
x = 0	unmounted
x = 12.7 g	glued on a copper heat sink with 12.7 mm diameter
x = 25.4 g	glued on a copper heat sink with 25.4 mm diameter

Low intensity spectral reflectance



Reverse design of the SAM-2900-9-x-10ps

